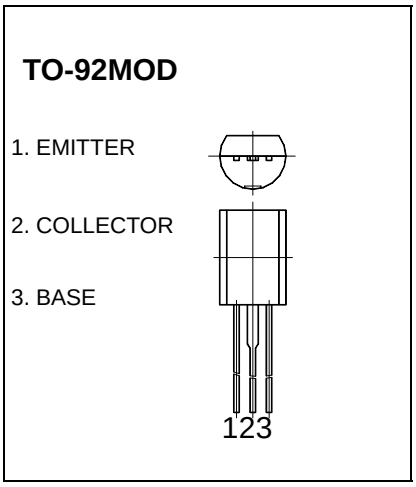
Transys Electronics LIMITED

TO-92MOD Plastic-Encapsulated Transistors

2SC1627A TRANSISTOR (NPN)



FEATURE

Power dissipation

P_{CM}: 0.8 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.4 A

Collector-base voltage

$V_{(BR)CBO}$: 80 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 100μA , I_E=0	80		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=5mA, IB=0	80		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}=50V, IE=0		0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, IC=0		0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=2 V, IC= 50mA	70	240	
	$h_{FE(2)}$	V_{CE}=2 V, IC= 200mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= 200m A, I_B= 20mA		0.4	V
Base-emitter voltage	$V_{BE(on)}$	V_{CE}= 2V, IC= 5mA	0.55	0.8	V
Transition frequency	f_T	V_{CE}= 10 V, I_C= 10mA	80		MHz

CLASSIFICATION OF hFE (1)

Rank	O	Y
Range	70-140	120-240